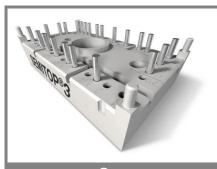
SK 60 DTA



SEMITOP® 3

3-phase bridge rectifier+ series thyristor

SK 60 DTA

Preliminary Data

Features

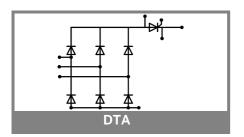
- · Compact design
- · One screw mounting
- · Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DBC)
- Glass passivated thyristor chips
 Reverse voltage up to 1600 V
- High surge currents

Typical Applications*

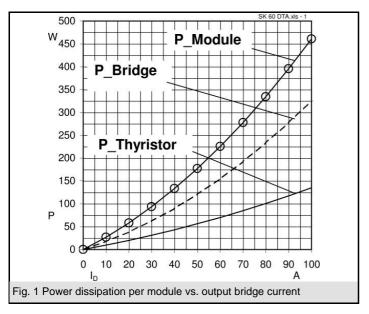
- Soft starters
- Light control
- Temperature control

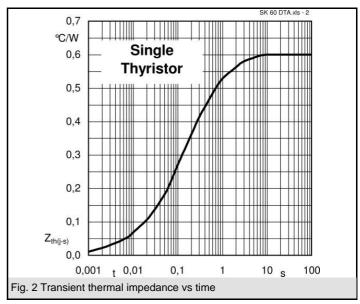
V _{RSM} V	V _{RRM} , V _{DRM} V	I _D = 61 A (T _s = 80 °C)
900	800	SK 60 DTA 08
1300	1200	SK 60 DTA 12
1700	1600	SK 60 DTA 16

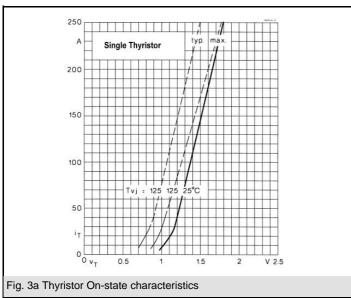
Characteristics T _s = 25°C unless otherwise specified				
Symbol	Conditions	Values	Units	
I _D	T _S = 80°C; Ind. load	61	Α	
I_{TAV}	sin. 180°; $T_s = 25 (80)$ °C per thyristor	86 (49)	Α	
I _{FAV}	sin. 180°; T _s = 25 (80) °C per diode	65 (45)	Α	
I _{TSM} /I _{FSM}	T _{vj} = 25 (125) °C; 10 ms	1500 (1350)	Α	
l²t	T_{vj} = 25 (125) °C; 8,3 10 ms	11250 (9100)	A²s	
T _{stg}		-40,+125	°C	
T _{solder}	terminals, 10 s	260	°C	
Thyristor			•	
(dv/dt) _{cr}	T _{vi} = 125 °C	1000	V/µs	
(di/dt) _{cr}	$T_{vi}^{3} = 125 ^{\circ}\text{C}; f = f = \text{Hz}$	50	A/μs	
t _q	$T_{vj} = 125 ^{\circ}\text{C}$; typ.	120	μs	
I _H	T _{vi} = 25 °C; typ. / max.	100 / 200	mA	
IL	$T_{vj} = 25 ^{\circ}\text{C}; R_{G} = 33 ^{\circ}\Omega; \text{typ. / max.}$	200 / 500	mA	
V _T	$T_{vi} = 25 ^{\circ}\text{C}; (I_T = 200 \text{A}); \text{max}.$	1,8	V	
V _{T(TO)}	T _{vi} = 125 °C	max. 0,9	V	
r _T	T _{vi} = 125 °C	max. 4,5	mΩ	
I _{DD} ; I _{RD}	T_{vj}^{y} = 125 °C; $V_{DD} = V_{DRM}$; $V_{RD} = V_{RRM}$	max. 20	mA	
R _{th(j-s)}	Cont. per thyristor	0,6	K/W	
T _{vj}		- 40 + 125	°C	
V _{GT}	$T_{vi} = 25 ^{\circ}\text{C}; \text{d.c.}$	2	V	
I _{GT}	$T_{vi}^{vj} = 25 ^{\circ}\text{C}; \text{d.c.}$	100	mA	
V _{GD}	$T_{vi}^{vj} = 125 ^{\circ}\text{C}; \text{d.c.}$	0,25	V	
I _{GD}	T _{vi} = 125 °C; d.c.	5	mA	
Diode	1	1	I	
V_{F}	$T_{vi} = 25 ^{\circ}\text{C}; (I_F = 75 \text{A}); \text{max}.$	1,45	V	
V _(TO)	T _{vi} = 125 °C	0,8	V	
r _T	T _{vi} = 125 °C	4,5	mΩ	
I _{RD}	T _{vj} = 125 °C; V _{RD} = V _{RRM}	2	mA	
R _{th(j-s)}	per diode	1	K/W	
T _{vi}		-40+150	°C	
Mechanic	al data	1	1	
V_{isol}	a. c. 50 Hz; r.m.s.; 1 s / 1 min	3000 (2500)	V	
M ₁	mounting torque	2,5	Nm	
	1	•		
W		30	g	

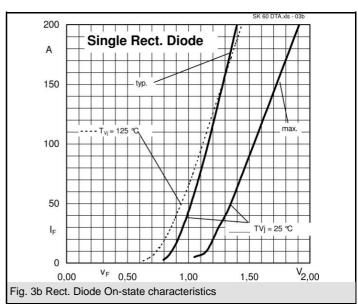


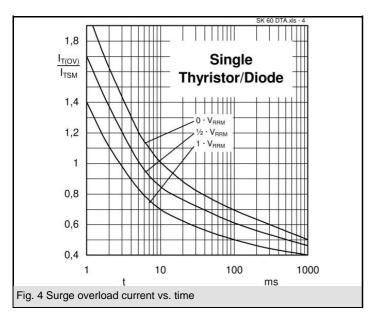
SK 60 DTA

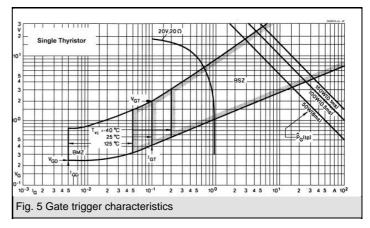


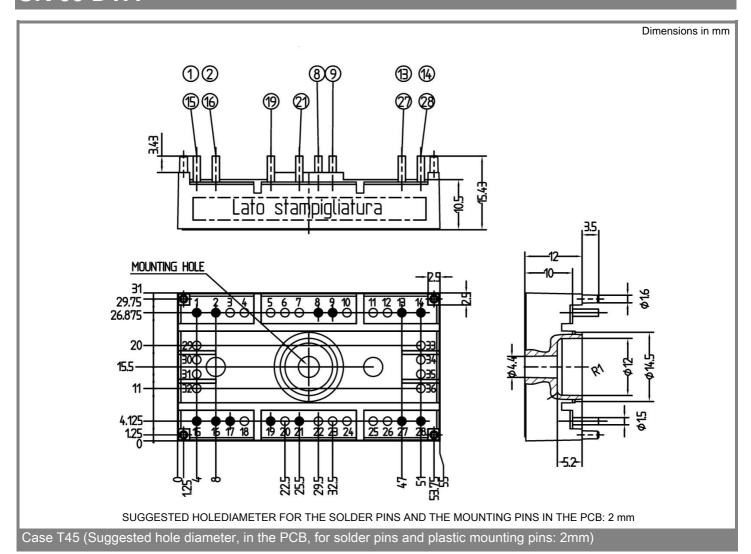


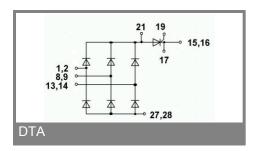












This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.